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(54) **STRUCTURE AND METHOD FOR VERTICAL TUNNELING FIELD EFFECT TRANSISTOR WITH LEVELED SOURCE AND DRAIN**

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**H01L 27/08** (2006.01)  
**H01L 29/66** (2006.01)  
**H01L 29/739** (2006.01)  
**H01L 49/02** (2006.01)  
**H01L 29/06** (2006.01)  
**H01L 21/8238** (2006.01)

(52) **U.S. Cl.**

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(58) **Field of Classification Search**

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USPC ..... **257/105**, **367**  
IPC ..... **H01L 29/7827**, **29/78642**, **29/88**  
See application file for complete search history.

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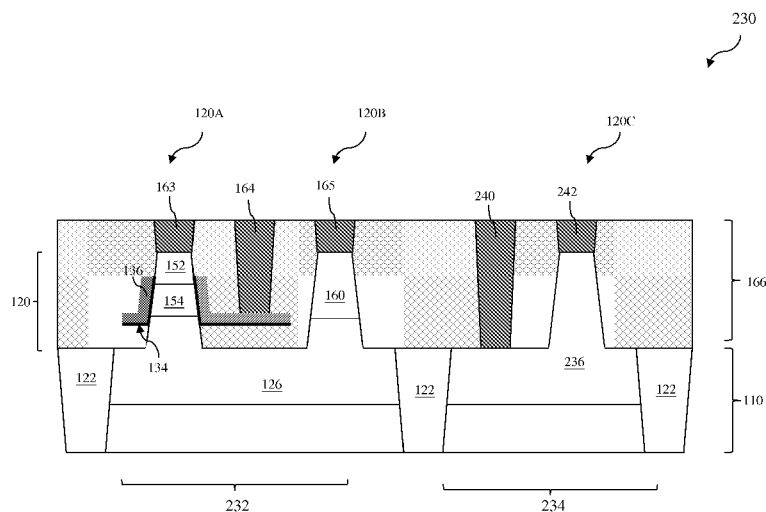
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(57) **ABSTRACT**

The present disclosure provides one embodiment of a semiconductor structure. The semiconductor structure includes a semiconductor substrate having a first region and a second region; a first semiconductor mesa formed on the semiconductor substrate within the first region; a second semiconductor mesa formed on the semiconductor substrate within the second region; and a field effect transistor (FET) formed on the semiconductor substrate. The FET includes a first doped feature of a first conductivity type formed in a top portion of the first semiconductor mesa; a second doped feature of a second conductivity type formed in a bottom portion of the first semiconductor mesa, the second semiconductor mesa, and a portion of the semiconductor substrate between the first and second semiconductor mesas; a channel in a middle portion of the first semiconductor mesa and interposed between the source and drain; and a gate formed on sidewall of the first semiconductor mesa.

**20 Claims, 15 Drawing Sheets**



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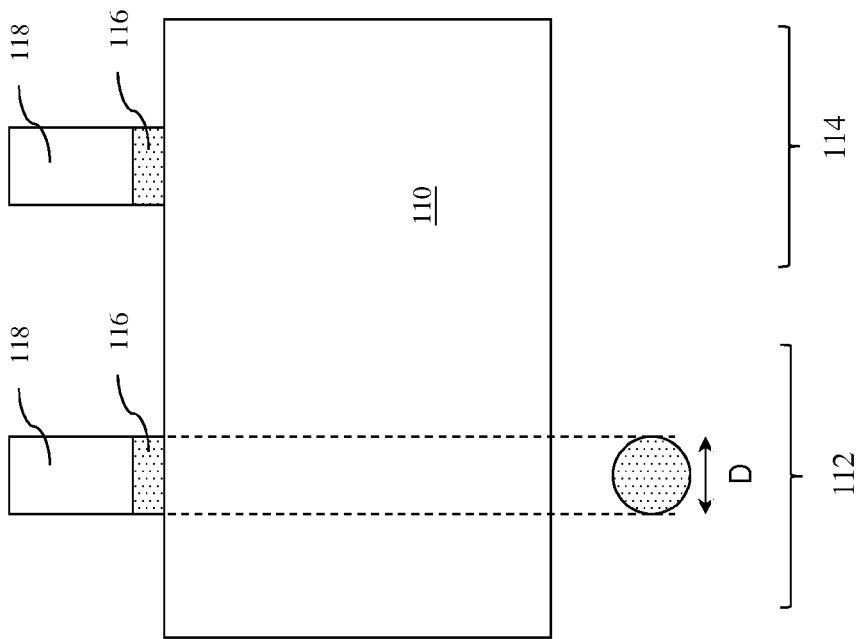


Fig. 1

100

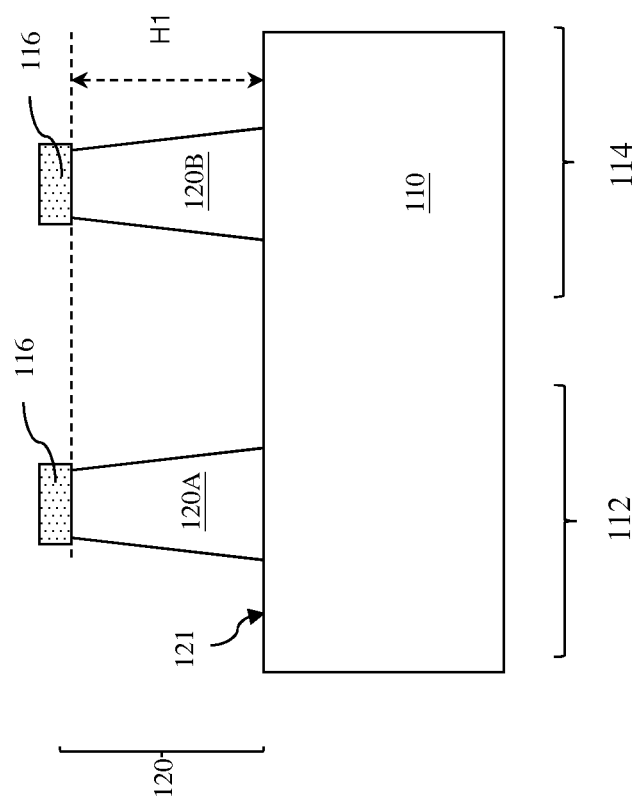


Fig. 2

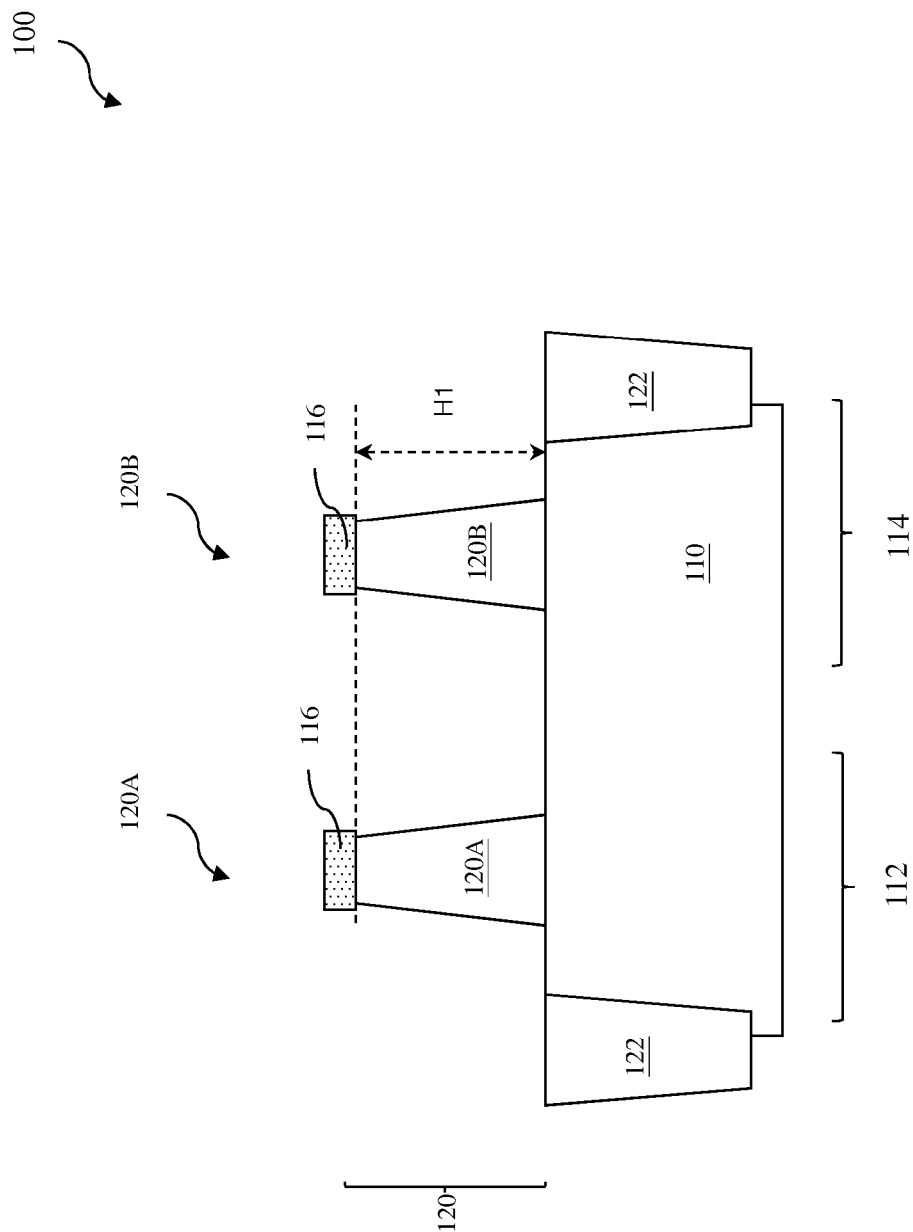


Fig. 3

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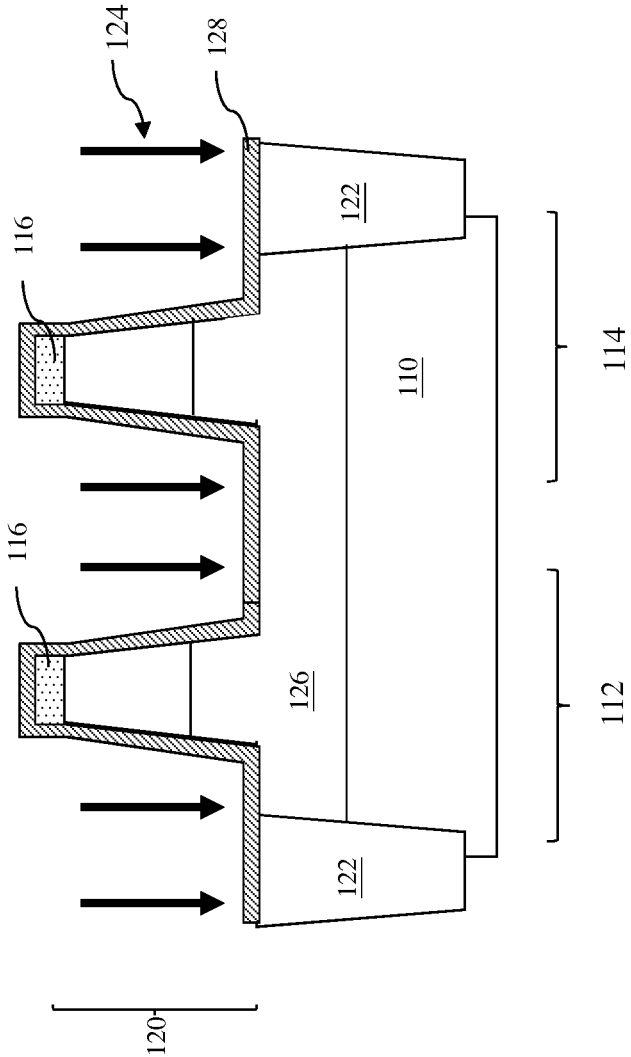
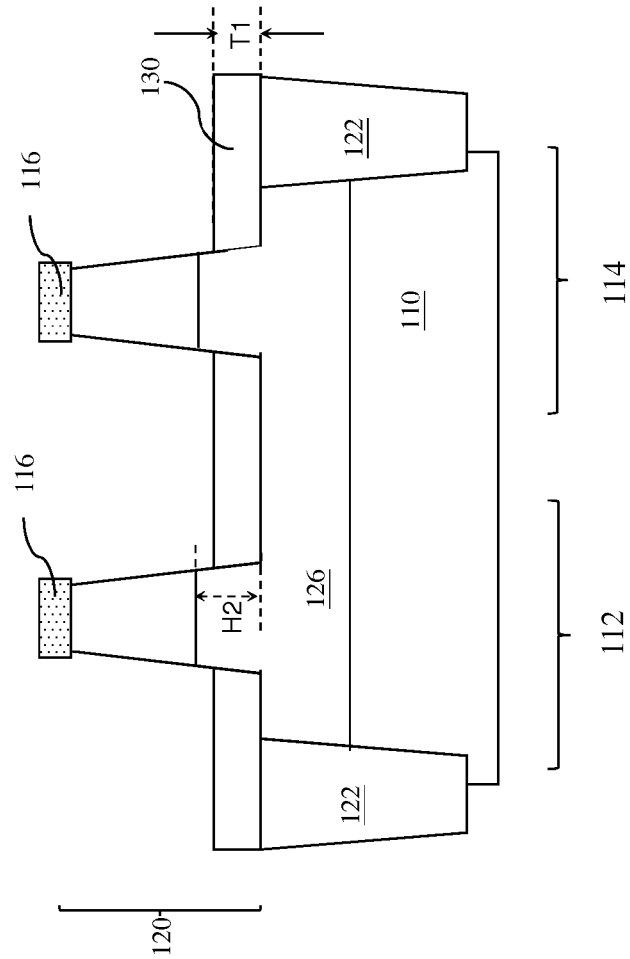
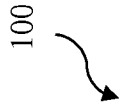


Fig. 4



**Fig. 5**

100

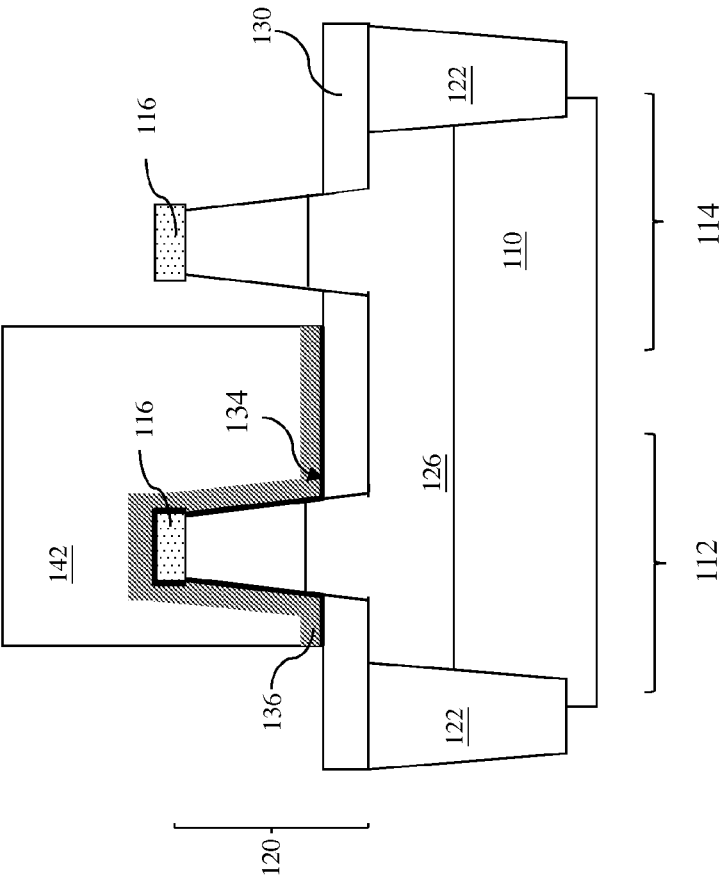


Fig. 6

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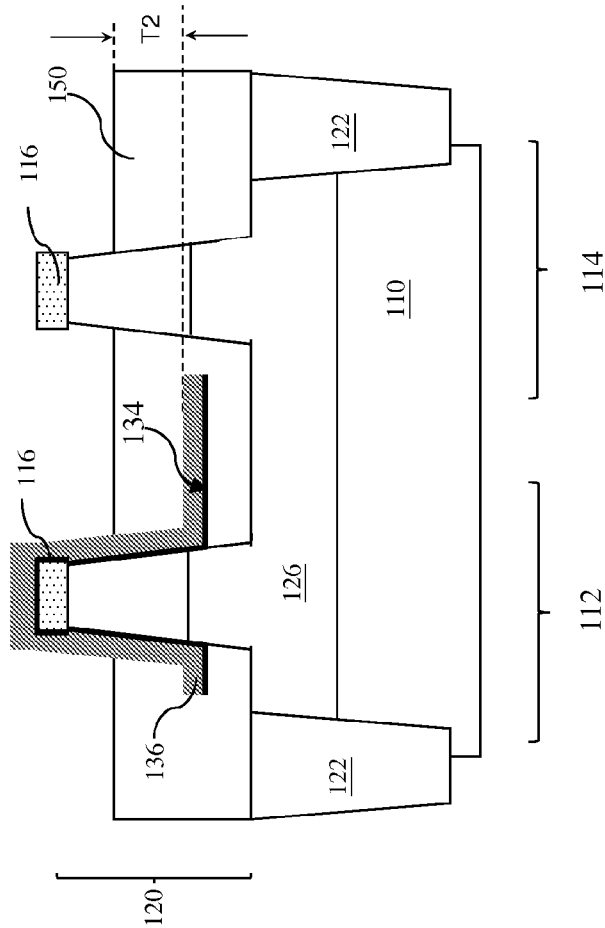
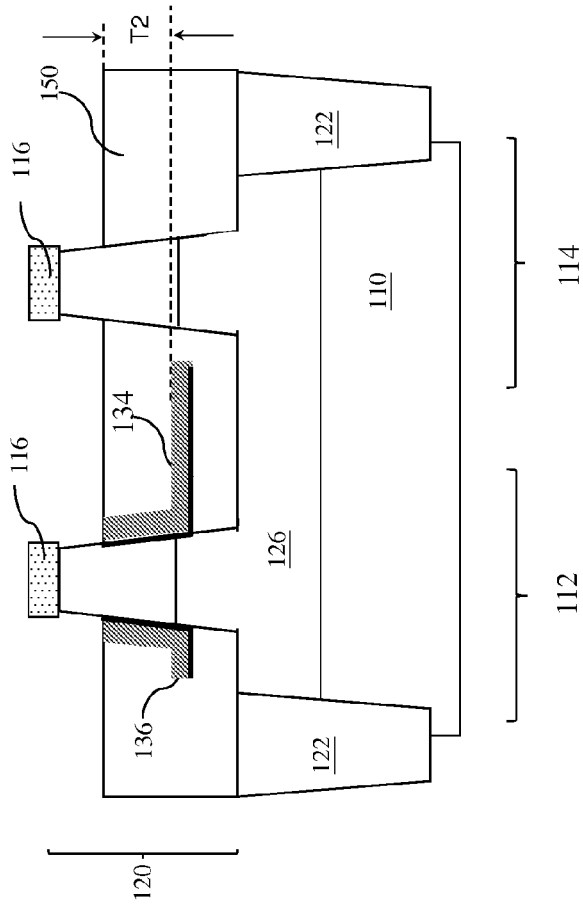
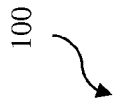
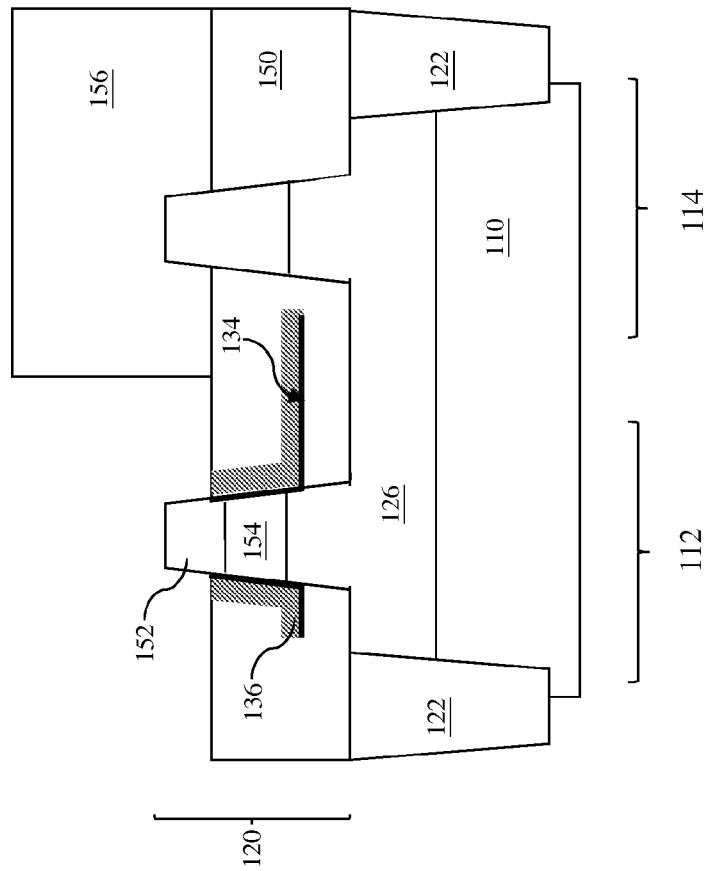
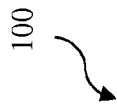


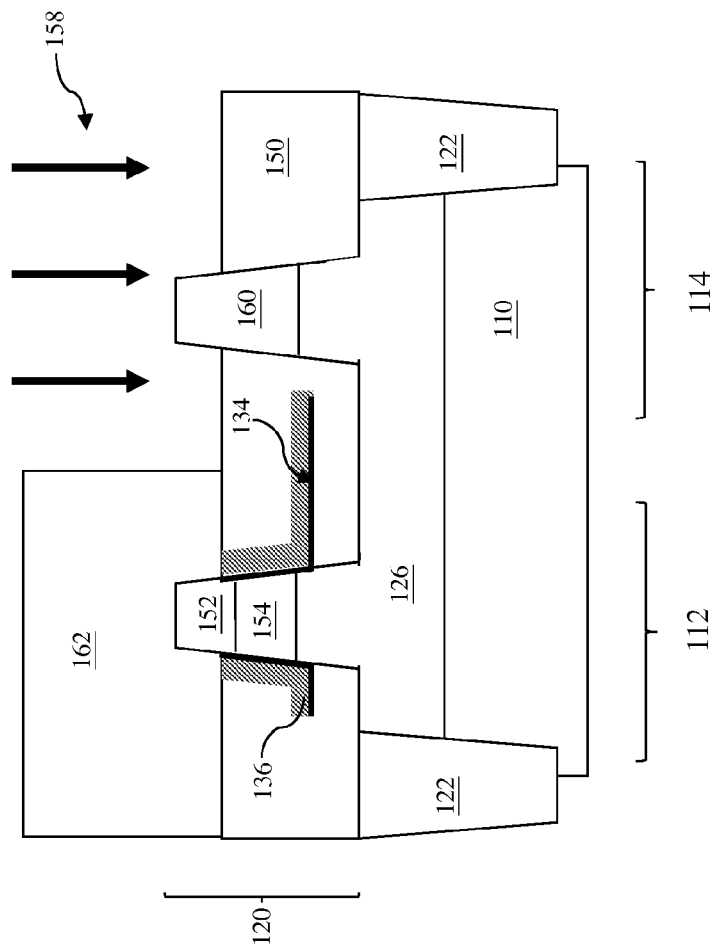
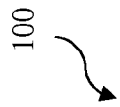
Fig. 7



**Fig. 8**



**Fig. 9**



**Fig. 10**

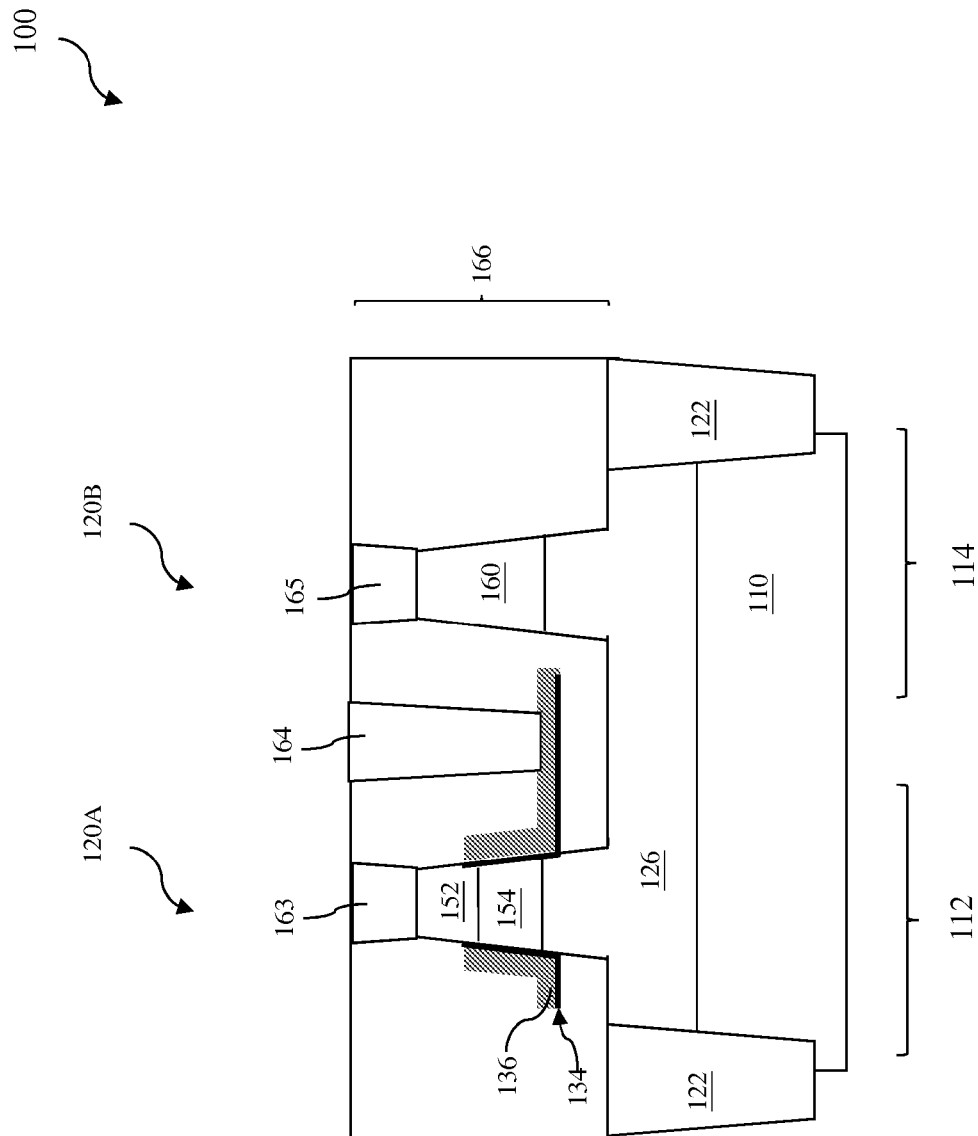


Fig. 11

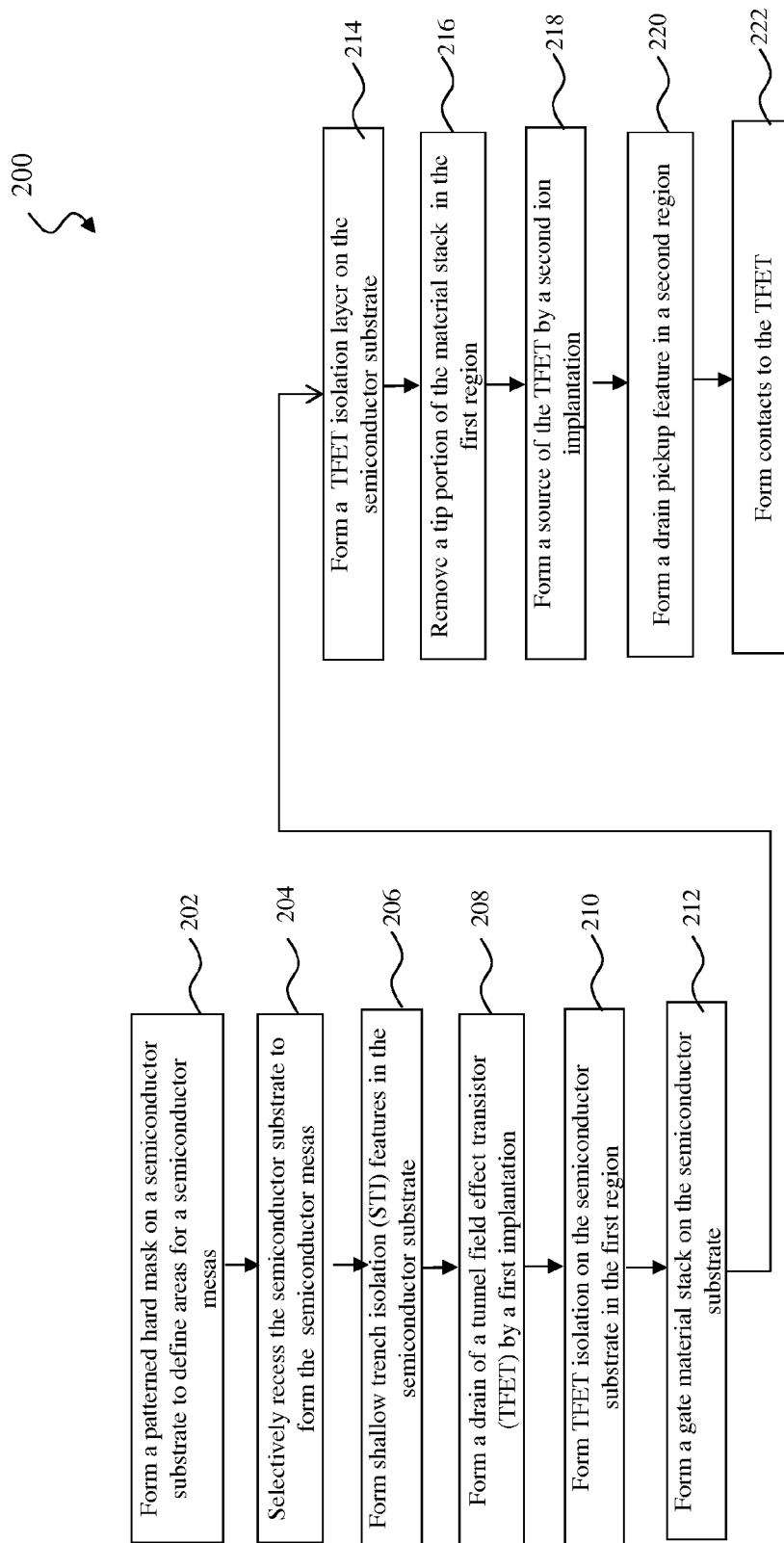


Fig. 12

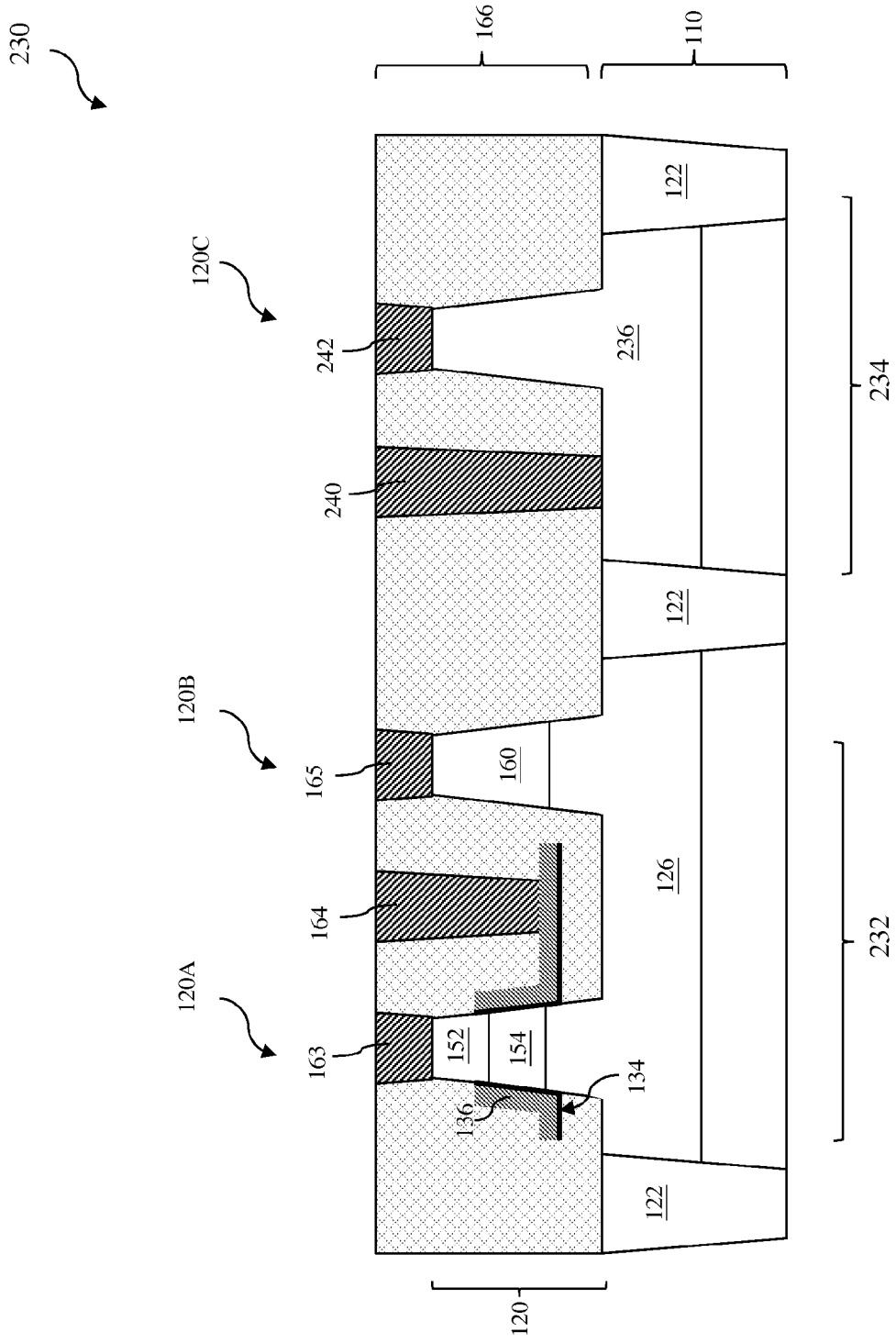
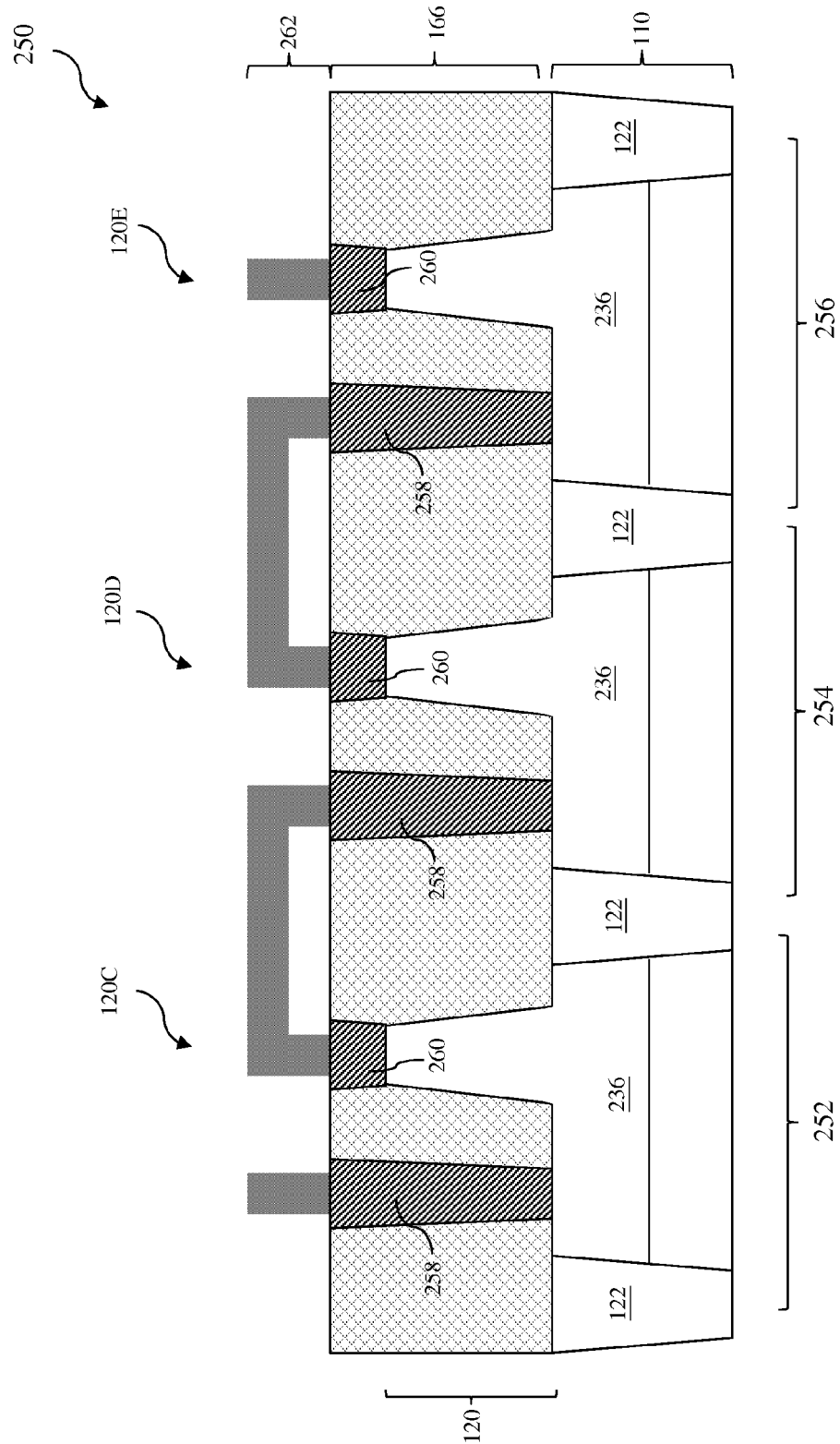
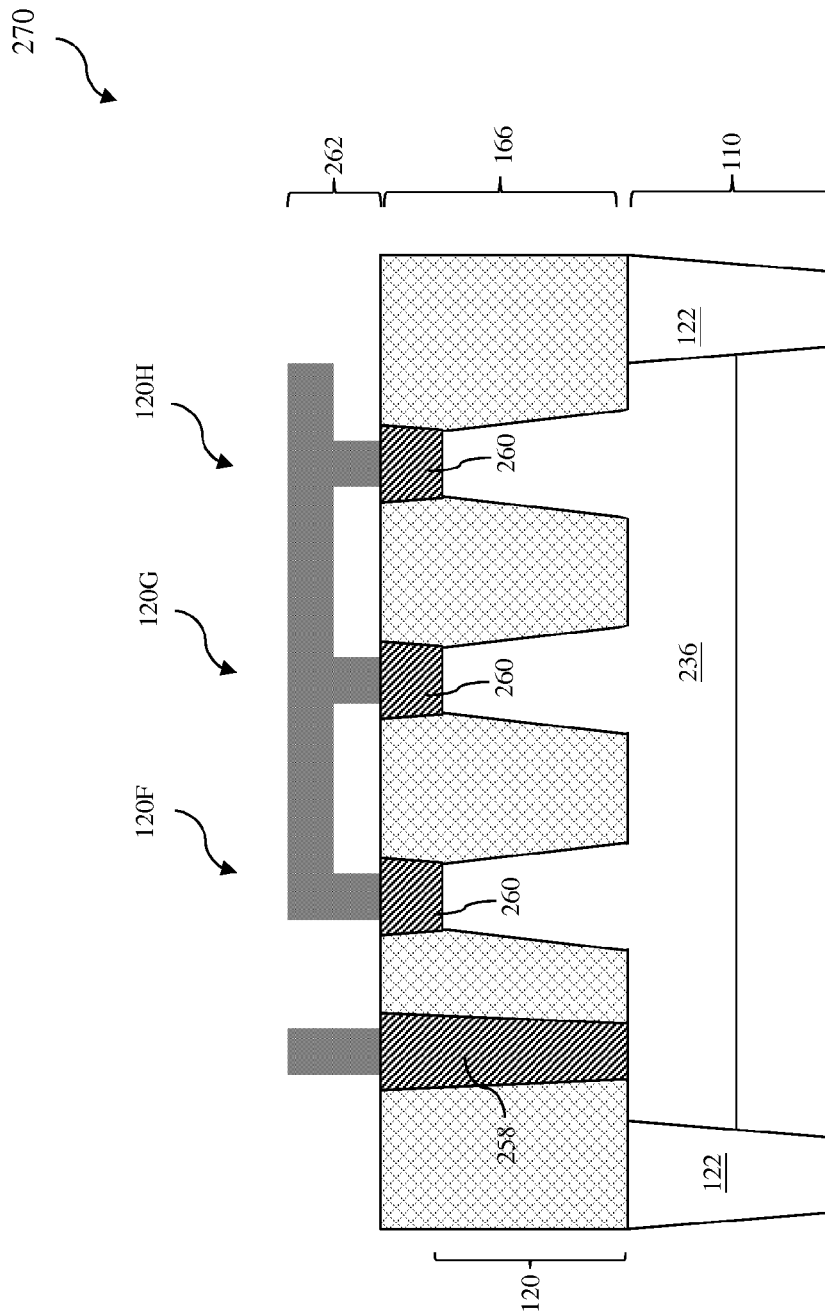


Fig. 13



**Fig. 14**



**Fig. 15**

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# STRUCTURE AND METHOD FOR VERTICAL TUNNELING FIELD EFFECT TRANSISTOR WITH LEVELED SOURCE AND DRAIN

## BACKGROUND

The scaling of conventional complementary metal-oxide-semiconductor field effect transistor (CMOSFET) faces challenges of rapid increase in power consumption. Tunnel field effect transistor (TFET) is a promising candidate enabling further scaling of power supply voltage without increase of off-state leakage current due to its sub-60 mV/dec subthreshold swing. However, in a vertical TFET, the source and drain are at different horizontal levels, which present various issues. For example, the contacts to the source and drain face more challenge due to the height difference.

Accordingly, there is a need for a structure having vertical TFET device and a method making the same to address above concerns.

## BRIEF DESCRIPTION OF THE DRAWINGS

Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is emphasized that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIGS. 1-11 are sectional views of a semiconductor structure having a tunnel field effect transistor (TFET) structure at various fabrication stages constructed according to one or more embodiments.

FIG. 12 is a flowchart of a method to form the semiconductor structure of FIG. 11 constructed according to one embodiment.

FIG. 13 is a sectional view of a semiconductor structure having a TFET structure and a capacitor constructed according to another embodiment.

FIG. 14 is a sectional view of a semiconductor structure having a resistor constructed according to another embodiment.

FIG. 15 is a sectional view of a semiconductor structure having a resistor constructed according to another embodiment.

## DETAILED DESCRIPTION

It is to be understood that the following disclosure provides many different embodiments, or examples, for implementing different features of various embodiments. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed. Moreover, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed interposing the first and second features, such that the first and second features may not be in direct contact.

FIGS. 1-11 are sectional views of a semiconductor structure 100 at various fabrication stages constructed according to

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one or more embodiment. The semiconductor structure 100 includes one or more tunnel field effect transistor (TFET). In furtherance of the embodiment, the TFET has a vertical structure wherein the channel is vertically configured and interposed between the source and drain. FIG. 12 is a flowchart of a method 200 to form the semiconductor structure 100 constructed according to one or more embodiment. The semiconductor structure 100 and the method 200 making the same are collectively described with reference to FIGS. 1-12.

Referring to FIG. 1, the semiconductor structure 100 includes a semiconductor substrate 110 of a first semiconductor material. In the present embodiment, the first semiconductor material is silicon. Alternatively, the first semiconductor material may include other proper semiconductor material. In one embodiment, the semiconductor substrate 110 includes a buried dielectric material layer for isolation formed by a proper technology, such as a technology referred to as separation by implanted oxygen (SIMOX). In some embodiments, the substrate 110 may be a semiconductor on insulator, such as silicon on insulator (SOI).

The semiconductor substrate 110 includes a first region 112 and a second region 114. The semiconductor substrate 110 includes a tunnel field effect transistor (TFET) formed in the first second regions. In the present embodiment, the TFET is a vertical TFET where the channel of the TFET is along a direction perpendicular to the top surface of the semiconductor substrate 110.

Referring to FIGS. 1 and 12, the method 200 begins at operation 202 by forming a patterned hard mask 116 to define areas for a first semiconductor mesa on the semiconductor substrate 110 within the first region 112 and a second semiconductor mesa on the semiconductor substrate 110 within the first region 112. Specifically, the patterned hard mask 116 includes a first feature in the first region 112 and a second feature in the second region 114. Each feature has a geometry defining the geometry of the corresponding semiconductor mesa. In the present embodiment, each feature of the patterned hard mask 116 has a round shape with a diameter D, which depends on the designed size of the corresponding semiconductor mesa and further depends on the fabrication bias. In one example, the diameter D ranges between about 10 nm and about 50 nm.

The patterned hard mask 116 includes a dielectric material with etch selectivity to the semiconductor substrate 110. In the present embodiment, the patterned hard mask 116 includes silicon nitride (SiN). In other embodiments, the patterned hard mask 116 alternatively includes other suitable material, such as silicon oxynitride or silicon carbide.

In one embodiment, the patterned hard mask 116 is formed by a procedure including deposition, lithography process and etching. In furtherance of the embodiment, the formation of the patterned hard mask 116 includes depositing a hard mask layer by a suitable technique, such as chemical vapor deposition (CVD); forming a patterned photoresist layer 118 on the hard mask layer using a lithography process; etching the hard mask layer to form the patterned hard mask 116 using the patterned photoresist layer 118 as an etch mask; and thereafter removing the patterned photoresist layer 118 by a suitable technique, such as wet stripping or plasma ashing. In one embodiment, the lithography process includes forming a photoresist layer by spin-on coating; exposing the photoresist layer using an exposure energy, such as ultraviolet (UV) light, and developing the exposed photoresist layer to form the patterned photoresist layer using a developing chemical. In another example, the lithography process includes spin-on coating, soft baking, exposing, post-exposure baking, developing and hard baking. In other embodiment, the lithography

process to form the patterned photoresist layer **118** may alternatively use other technique, such as e-beam lithography, maskless patterning or molecular print.

Referring to FIGS. 2 and 12, the method **200** includes an operation **204** by selectively recessing the semiconductor substrate to form semiconductor mesas **120**, especially the first semiconductor mesa **120A** in the first region **112** and the second semiconductor mesa **120B** in the second region **114**.

In the present embodiment, the first and second semiconductor mesas have a coplanar top surface. The semiconductor mesas (**120A** and **120B**) have a height “H1” as a vertical dimension relative to the top surface **121** of the semiconductor substrate **110**. In one example, the recess depth ranges between about 50 nm and about 200 nm. Therefore, the height H1 of the semiconductor mesas **120** is in the same range for this example.

The first and second semiconductor mesas are simultaneously formed in a same procedure. In the present embodiment, an etch process is applied to selectively etch the semiconductor substrate **116** using the patterned hard mask **116** as an etch mask. For example, the etch process includes a dry etch to etch silicon of the semiconductor substrate **110**. In one embodiment, the etch process is tuned to form the semiconductor mesa **120A** (**120B** as well) having a sidewall profile in a trapezoidal shape. Particularly, the sidewall profile of the each semiconductor mesa has a tilting angle less than 90° and greater than 45°, where the tilting angle is measured relative to the top surface **121** of the semiconductor substrate **110**. Thus formed the semiconductor mesa (**120A** or **120B**) has a better fabrication benefits during the subsequent process steps, such as deposition and/or etch.

Referring to FIGS. 3 and 12, the method **200** includes an operation **206** by forming a plurality of isolation features **122** in the semiconductor substrate **110**. In the present embodiment, the isolation features **122** are shallow trench isolation (STI) features **122**. The STI features **122** are formed in the semiconductor substrate **110** and define various active regions. In this case, the first region **112** and the second region **114** are within a same active region. Furthermore, the top surface **121** of the semiconductor substrate **110** and top surfaces of the STI features **112** are coplanar at the present fabrication stage.

Since the presence of the semiconductor mesas **120**, the formation of the STI features **122** is designed to avoid the damage to the semiconductor mesas **120**.

In one embodiment, the formation of the STI features **122** includes: forming a hard mask with openings that define the regions for STI features; etching the semiconductor substrate **110** through the openings of the hard mask to form trenches; depositing dielectric material to fill in the trenches; performing a chemical mechanical polishing (CMP) process to remove excessive dielectric material above the semiconductor mesa **120**; and then selectively etching back the dielectric material to the top surface of the semiconductor substrate **110**, resulting in the STI features **122**. In the CMP process, the patterned hard mask **116** may serve as a polishing stop layer such that the CMP process properly stops on the patterned hard mask **116**. In the etch-back process, the patterned hard mask **116** may serve as an etch mask to further protect the semiconductor mesas **120** from loss.

In another embodiment, the STI features **122** are formed before the formation of the semiconductor mesas **120**. In furtherance of the embodiment, the formation of the STI features **122** includes: forming a hard mask with openings that define the regions for STI features; etching the semiconductor substrate **110** through the openings of the hard mask to form deep trenches; depositing dielectric material to fill in the

trenches; and performing a CMP process to remove excessive dielectric material above the semiconductor substrate **110**, resulting in deep trench isolation features. Thereafter, the operations **202** and **204** are performed to form the patterned hard mask **116** and to form the semiconductor mesas **120**, respectively. However, in the operation **204** to recess the semiconductor substrate **110** by an etch process, the etch process is designed to recess both the semiconductor material (silicon in the present embodiment) of the semiconductor substrate **110** and the dielectric material of the deep trench isolation features. Thus, the upper portions of the deep trench isolation features are removed, resulting in shallow trench isolation features **122**. The height difference between the deep trench isolation features and the STI features **122** is about the height H1 of the semiconductor mesa **120**.

In another embodiment, the deposition of the dielectric material includes thermal oxidation of the trenches and then filling in the trenches by the dielectric material, such as silicon oxide, by CVD. In one example, the CVD process to fill in the trenches includes high density plasma CVD (HD-PCVD).

Referring to FIGS. 4 and 12, the method **200** includes an operation **208** to form the drain **126** of the TFET by a first ion implantation process **124**. The drain **126** is formed in the bottom portion of the first semiconductor mesa **120**, the bottom portion of the first semiconductor mesa **120** and a portion of the semiconductor substrate **110** below the top surface **121**. The drain **126** is a continuous doped feature extending from the first semiconductor mesa **120A** to the second semiconductor mesa **120B** through the semiconductor substrate **110**. In the present embodiment, the drain **126** includes a n-type dopant (such as phosphorous) when the TFET is n-type or a p-type dopant (such as boron) when the TFET is p-type.

In one embodiment, the operation **208** includes depositing a screening layer **128** on the semiconductor substrate **110** and the semiconductor mesas **120**; and performing a selective implantation to the semiconductor substrate **110** and the semiconductor mesas **120**. The screening layer **128** is used for implantation screening and elimination of the channeling effect during the implantation.

Particularly, the selective implantation includes forming a patterned photoresist layer on the semiconductor substrate **110**, performing the ion implantation process **124** using the patterned photoresist layer as an implantation mask, and removing the patterned photoresist layer thereafter by wet stripping or plasma ashing. The patterned photoresist layer covers other regions not intended for the ion implantation process **124**. The patterned photoresist layer is formed by a lithography process as described above.

The drain **126** formed by the ion implantation **124** is further annealed for activation by an annealing process. The annealing process is implemented right after the ion implantation **124** in the operation **208** or is alternatively implemented after the formation of other doped features for collective activation. In one embodiment, the annealing process includes rapid thermal annealing (RTA). In other embodiments, the annealing process alternatively includes laser annealing, spike annealing, million second anneal (MSA) or other suitable annealing technique.

Referring to FIGS. 5 and 12, the method **200** includes an operation **210** to form a TFET isolation layer **130**. The TFET isolation layer **130** provides isolation function to and properly configures various features of the TFET. For examples, the gate is properly aligned with the channel, not directly formed on the semiconductor substrate **110**, and is substantially off from the drain.

The TFET isolation layer **130** includes a dielectric material, such as silicon oxide in the present example. The TFET isolation layer **130** may alternatively include other suitable dielectric material. The TFET isolation layer **130** is disposed on the semiconductor substrate **110**. Particularly, the thickness **T1** of the TFET isolation layer **130** is chosen such that the subsequent formed gate can be properly configured with the channel and the drain. As illustrated in FIG. 5, “H2” is the height of the drain **126** measured from the top surface of the semiconductor substrate **110** up to the top surface of the drain **126**. The thickness **T1** of the TFET isolation layer **130** is chosen such that **T1** is little less than **H1** as **T1**<**H1**, to have a small overlap between the gate and drain, and to further ensure that the gate completely couples with the channel.

In one embodiment, the operation **210** includes removing the screen layer **128** by an etch process (such as a wet etch); and forming a dielectric material layer (such as silicon oxide in the present embodiment) on the semiconductor substrate **110**. In one embodiment, the forming of the dielectric material layer includes depositing a dielectric material, performing a CMP process to remove a portion of the dielectric material above the semiconductor mesas **120**, and etch back the dielectric material. In another embodiment, the dielectric material layer is selectively removed from other regions by a procedure including forming a patterned photoresist layer on the semiconductor substrate **110**, performing an etch process to the dielectric material layer using the patterned photoresist layer as an etch mask, and removing the patterned photoresist layer thereafter by wet stripping or plasma ashing.

Referring to FIGS. 6 and 12, the method **200** includes an operation **212** to form gate stack on the semiconductor substrate **110**. The formation of the gate stack includes forming gate material layers and patterning the gate material layers to form the gate stack.

The gate material layers are formed on the first semiconductor mesa **120A** and on the TFET isolation layer **130**. Especially, the gate material layers are formed on sidewalls of the first semiconductor mesa **120A** and on the top surface thereof as well. In the present case, the gate material layers are disposed on the patterned hard mask **116**.

The gate material layers include gate a dielectric material layer **134** and a gate electrode layer **136**. In the present embodiment, the gate material layers include high k dielectric material and metal, therefore, referred to as high k metal gate. In one embodiment, the gate dielectric material layer **134** includes an interfacial layer (such as silicon oxide) and a high k dielectric material layer. A high k dielectric material is a dielectric material having a dielectric constant greater than that of thermal silicon oxide. For example, a high k dielectric material includes hafnium oxide (HfO) or other suitable metal oxide. The gate electrode layer **136** includes a metal (or metal alloy) layer and may further include a polycrystalline silicon (polysilicon) layer on the metal layer.

The operation **212** includes depositing various gate materials on the semiconductor substrate, specifically on the TFET isolation feature **130** and the semiconductor mesas **120**. Especially as described in one embodiment where the semiconductor mesa **120A** has a trapezoidal profile, it is beneficial for depositions of various gate materials. In one embodiment, the formation of the interfacial layer (silicon oxide in the present example) includes thermal oxidation, ALD, CVD or other suitable technology. In another embodiment, the formation of the high k dielectric material layer includes ALD, metalorganic CVD (MOCVD), physical vapor deposition (PVD), or other suitable technology. In yet another embodiment, the formation of the metal layer includes PVD, plating, or other

suitable technology. In yet another embodiment, the formation of the polysilicon layer includes CVD or other suitable technology.

The operation **212** also includes patterning the gate material layers including the gate dielectric material layer **134** and the gate electrode layer **136**, resulting in a gate material stack in the first region **112**. The material stack includes a first portion on the top of the first semiconductor mesa **120A**, a second portion on the sidewall of the first semiconductor mesa **120A**, and a third portion on the top surface of the TFET isolation layer **130**. The third portion of the material stack is horizontally extended on the TFET isolation layer **130**.

In one embodiment, the patterning of the gate material layers includes forming a patterned photoresist layer **142** on the gate material layers, performing an etch process to the gate material layers using the patterned photoresist layer **142** as an etch mask, and removing the patterned photoresist layer **142** thereafter by wet stripping or plasma ashing. In one example, the etch process includes more than one etch steps using different etchants to etch respective materials in the gate material layers. Each etchant is designed to effectively etch the respective material. The patterned photoresist layer **142** is formed by a lithography process. The patterned photoresist layer **142** covers the semiconductor substrate **110** in the first region **112**, as illustrated in FIG. 6.

Referring to FIGS. 7 and 12, the method **200** may include an operation **214** to form a TFET isolation layer **150** on the semiconductor substrate **110**. The TFET isolation layer **150** provides isolation function to and properly configures various features of the TFET. For examples, the source of the TFET is properly configured thereby.

The TFET isolation layer **150** includes a dielectric material, such as silicon oxide in the present example. The TFET isolation layer **150** may alternatively include other suitable dielectric material, such as low k dielectric material. The TFET isolation layer **150** is disposed on the semiconductor substrate **110**, the TFET isolation layer **130** and the gate material stack. Particularly according to the present embodiment, the thickness of the TFET isolation layer **150** is chosen such that a remaining isolation thickness **T2** is about 1/3 of the total vertical height of the semiconductor mesa **120**. The remaining isolation height **T2** is a vertical dimension measured from the top surface of the horizontal portion of the material stack up to the top surface of the TFET isolation layer **150**. The length of the channel is associated with the remaining isolation thickness **T2** and is determined thereby.

In one embodiment, the operation **214** includes deposition of the dielectric material (silicon oxide in the present example), performing a CMP process to remove excessive dielectric material above the semiconductor mesa **120**, and etching back to recess the dielectric material to reach the desired thickness range.

In the present embodiment, the TFET isolation layer **130** and the TFET isolation **150** both include silicon oxide and are collectively labeled with numeral **150** in FIG. 7.

Referring to FIGS. 8 and 12, the method **200** includes an operation **216** to remove a portion of the gate material stack uncovered by the TFET isolation layer **150**. The operation **216** includes an etch process to selectively etch the gate material layers in the top portion of the gate material stack. The etch process may include more than one steps tuned to etch respective gate material layers. By removing the top portion of the gate material stack, the gate of the corresponding TFET is formed on the sidewall of the middle portion of the first semiconductor mesa **120A** with a horizontal extending portion for contact.

Referring to FIGS. 9 and 12, the method 200 includes an operation 218 to form a source 152 of the TFET device in the first semiconductor mesa 120A. In the present embodiment, the source 152 is formed in the top portion of the first semiconductor mesa 120A. Particularly, the drain 126 has a first type conductivity and the source 152 has a second type conductivity that is opposite from the first type conductivity. For example, if the first type conductivity is n-type (or p-type), the second type conductivity is p-type (or n-type). In one embodiment where the TFET is n-type, the drain 126 includes a n-type dopant (such as phosphorous) and the source 152 includes a p-type dopant (such as boron). In another embodiment where the TFET is p-type, the drain 126 includes a p-type dopant and the source 152 includes a n-type dopant. A channel 154 is defined in the middle portion of the first semiconductor mesa 120A.

In one embodiment, the operation 218 includes removing the hard mask 116, forming a patterned photoresist layer on the TFET isolation layer 156, performing the ion implantation process using the patterned photoresist layer as an implantation mask, and removing the patterned photoresist layer 156 thereafter. The patterned photoresist layer 156 has an opening configured such that the first semiconductor mesa 120A is uncovered by the patterned photoresist layer. During the ion implantation, the TFET isolation layer 150 serves as an implantation mask in addition to the patterned photoresist layer 156 so that only the top portion of the first semiconductor mesa 120A is implanted thereby.

In yet another embodiment, the operation 218 further includes recessing the first semiconductor mesa 120A and epitaxy growing on the recessed semiconductor mesa 120A with a semiconductor material that is same to that of the semiconductor substrate 110 (such as silicon) or different (such as silicon germanium). Dopant of the source 152 may be introduced by an ion implantation by in-situ doping. In the in-situ doping, the epitaxy growth includes a precursor having the corresponding dopant chemical so that the dopant is simultaneously formed during the epitaxy growth. This method may achieve a high doping concentration of the source 152. In a particular example, the operation 218 includes removing the hard mask 116, recessing a portion of the semiconductor mesa 120A by an etch process, and epitaxy growing on the recessed semiconductor mesa with in-situ doping. According to one embodiment, by recessing and epitaxy growth, thus formed source 152 has a smoother interface between the source and the channel. Furthermore, the corresponding junction has an enhanced performance. When a different semiconductor material is epitaxy grown for the source, a proper strain effect may be generated for the enhanced mobility and device performance.

The operation 218 may further include an annealing process to anneal the source 152 for activation. The annealing process may be implemented right after the corresponding ion implantation (or epitaxy growth) or is alternatively implemented after the formation of other doped features for collective activation. In various examples, the annealing process includes RTA, laser annealing, spike annealing, MSA, or other suitable annealing technique.

The channel 154 is defined between the source 152 and the drain 126. Particularly, the channel 154 is defined in the middle portion of the first semiconductor mesa 120A. The channel 154 is vertically configured so that the current of the TFET vertically flows through the channel 154 from the source 152 to the drain 126.

In one embodiment, the channel 154 is neutral (un-doped). In another embodiment, the channel is lightly doped. In one example, the channel 154 has a conductivity type same to the

conductivity type of the drain 126. For instance, the channel has a n-type dopant when the TFET is n-type, or the channel has a p-type dopant when the TFET is p-type. In this case, the doping concentration of the channel 154 is substantially less than that of the drain 126.

In the present embodiment, the source 152 has a small overlap with the gate stack of the TFET to ensure that the channel 154 is completely coupled with and controlled by the gate stack.

Referring to FIGS. 10 and 12, the method 200 includes an operation 220 to perform an ion implantation 158 to form the drain pickup feature 160 of the TFET. The drain pickup feature 160 is formed in a top portion of the second semiconductor mesa 120B. The drain pickup feature 160 has a same type of conductivity as that of the drain 126 and is contacted with the drain 126 but has a doping concentration greater than that of the drain 126 to reduce the contact resistance. In the present embodiment, the drain pickup feature 160 includes a n-type dopant (such as phosphorous) when the TFET is n-type or a p-type dopant (such as boron) when the TFET is p-type.

In one embodiment, the operation 220 includes forming a patterned photoresist layer 162 to cover the first semiconductor mesa 120A in the first region 112; and performing the ion implantation 158 to the second semiconductor mesa 120B using the patterned photoresist layer 162 as an implantation mask, and removing the patterned photoresist layer thereafter by wet stripping or plasma ashing.

The drain pickup feature 160 formed by the ion implantation 158 may be further annealed for activation by an annealing process. The annealing process may be implemented after the ion implantation 158 in the operation 220 or is alternatively implemented after the formation of other doped features for collective activation.

Referring to FIGS. 11 and 12, the method 200 may further include an operation 222 to form various contacts to the TFET. In the present embodiment, the contacts 163, 164 and 165 are formed in an interlayer dielectric (ILD) 166. The contact 163 is configured to land on the first semiconductor mesa 120A and is electrically connected to the source 152. The contact 164 is configured to land on the horizontal portion of the gate and is electrically connected to the gate. The contact 165 is configured to land on the second semiconductor mesa 120B and is electrically connected to the drain pickup feature 160, therefore is electrically connected to the drain 126. Particularly, the source contact 163 and the drain contact 165 have a same height since the drain has a raised structure such that the source and drain are in the same horizontal level.

In FIG. 11, the ILD 166 collectively refers to the dielectric material layers that include the TFET isolation layer 130 and the TFET isolation layer 150 and further include a dielectric material layer deposited on the TFET isolation layer 150. The ILD 166 includes silicon oxide or a low k dielectric material or other suitable dielectric material. In various embodiment, the ILD 166 includes silicon oxide, silicon nitride, silicon oxynitride, polyimide, spin-on glass (SOG), fluoride-doped silicate glass (FSG), carbon doped silicon oxide, low-k dielectric material, and/or other suitable materials. The ILD 166 may be formed by a technique including spin-on, CVD, sputtering, or other suitable processes.

The contacts are conductive components in the interconnect structure and provide electrical routing between the devices and the metal line in the vertical direction. In one embodiment, the operation 222 includes depositing a dielectric material layer for the ILD, performing a CMP process to planarize the ILD, forming a patterned mask layer having a

plurality of openings to define the regions for the contacts, etching to form the contact holes using the patterned mask layer as an etch mask, filling a conductive material in the contact holes, and performing another CMP process to remove the excessive conductive material formed on the ILD. The patterned mask layer may be a patterned hard mask layer or alternatively a patterned photoresist layer. The patterned hard mask layer is similar to the patterned hard mask **116** in terms of formation and composition. The formation of the patterned photoresist layer is similar to that of the other patterned photoresist layers previously described. The conductive material of the contacts includes metal, metal alloy or other suitable conductive material. In the present embodiment, the conductive material of the contacts includes tungsten (W). The contacts may further include other material. For example, the contacts include a lining layer, such as titanium nitride or tantalum nitride, formed on the sidewalls of the contact holes before the filling of the conductive material to the contact holes. The filling of the conductive material in the contact holes may use a suitable technology, such as CVD or plating.

The operation **222** may further include forming other interconnect features and other fabrication steps (such as passivation) in the backend of the line. The interconnect structure includes horizontal conductive features (metal lines) and vertical conductive features (such as vias and contacts). The interconnect structure includes conductive materials such as aluminum, aluminum/silicon/copper alloy, titanium, titanium nitride, tungsten, polysilicon, metal silicide, or combinations, being referred to as aluminum interconnects. Aluminum interconnects may be formed by a process including physical vapor deposition (or sputtering), chemical vapor deposition (CVD), or combinations thereof. Other manufacturing techniques to form the aluminum interconnect may include photolithography processing and etching to pattern the conductive materials for vertical (via and contact) and horizontal connects (conductive line). Alternatively, a copper multilayer interconnect may be used and include copper, copper alloy, titanium, titanium nitride, tantalum, tantalum nitride, tungsten, polysilicon, metal silicide, or combinations. The copper multilayer interconnect may be formed by a technique such as CVD, sputtering, plating, or other suitable process. The metal silicide used in multilayer interconnects may include nickel silicide, cobalt silicide, tungsten silicide, tantalum silicide, titanium silicide, platinum silicide, erbium silicide, palladium silicide, or combinations thereof.

Other fabrication steps may be implemented before, during and after the operations of the method **200**.

Thus formed semiconductor structure **100** includes a vertical TFET and may further include another device integrated with the vertical TFET in a circuit. In one embodiment, the source and drain are leveled, the source contact and the drain contact have a same height, the source and drain contacts can be formed in a same procedure with less fabrication cost and improved performance and reliability. In another embodiment, the raised drain structure may be used as a resistor, as various embodiments described below.

The method **200** and the semiconductor structure **100** made thereby are described above in various embodiments. However, the present disclosure may include other alternatives and modifications. For example, the source and drain are switched such that the drain is formed on the top portion of the first semiconductor mesa **120A**, and the source is formed on the bottom portion of the first semiconductor mesa **120A** and is extended to the second semiconductor mesa **120B** through the semiconductor substrate **110**.

FIG. **13** is a sectional view of a semiconductor structure **230** constructed according to another embodiment of the present disclosure. Similar descriptions (including features and operations to form the features) are eliminated for simplicity. The semiconductor structure **230** includes a vertical TFET in the first active region **232** and a resistor in the second active region **234**. In this embodiment, the vertical TFET is similar to the one in FIG. **11** and the resistor in the second active region **234** is formed in a third semiconductor mesa **120C** in the second active region **234** and is further extended to the semiconductor substrate **110**. Particularly, the resistor has a continuous doped feature **236** including a vertical portion formed in the third semiconductor mesa **120C** and a horizontal portion formed in the semiconductor substrate **110**. The resistor is a two terminal passive device with two contacts **240** and **242** contacting to the two ends of the resistor. The contact **240** lands on the semiconductor substrate **110** and contacts to one end of the doped feature **236**. The contact **242** lands on the third semiconductor mesa **120C** and contacts to another end of the doped feature **236**.

The semiconductor structure **230** is formed by a method similar to the method **200**. In one embodiment, the doped feature **236** is formed by the operation **208** to form the drain **126**. In one example, the hard mask **116** on the third semiconductor mesa **120C** is removed and the operation **208** is executed thereafter so that the corresponding implantation process **124** introduce the dopant into the top portion of the third semiconductor mesa **120C** as well and the doped features **236** is thus extended from the top surface of the third semiconductor mesa **120C** to the semiconductor substrate **110** within the second active region **234**.

In another embodiment, the doped feature **236** is formed in the operation **220** to form the drain pickup feature **160**. In this case, the TFET isolation layers **130** and **150** are patterned in the corresponding operations such that the second active region **234** is not covered by the TFET isolation layers.

In another embodiment, the doped region **236** is formed by a separate ion implantation. Since the doped feature **236** functions as a resistor, the resistance of the resistance thus can be tuned by the dopant concentration.

As noted above, two contacts **240** and **242** are formed on two sides of the doped feature **236**. In other embodiment, more contacts are formed on two sides of the doped feature **236**. For example, multiple contacts are formed on the left side of the doped feature **236** and are configured along the left side, serving as a first terminal of the resistor. Multiple contacts are formed on the right side of the doped feature **236** and are configured along the right side, serving as a second terminal of the resistor.

FIG. **14** is a sectional view of a semiconductor structure **250** constructed according to another embodiment of the present disclosure. The semiconductor structure **250** includes a plurality of resistors connected in series. FIG. **14** only shows three resistors for illustration. Each resistor is similar to the resistor of FIG. **13** and is formed by the same method. The semiconductor structure **250** includes a plurality of STI features **122** formed in the semiconductor substrate **110**, defining a plurality of active regions, such as active regions **252**, **254** and **256** in the present example. Each active region includes a semiconductor mesa, such as semiconductor mesas **120C**, **12D** and **120E** in the active regions **252**, **254** and **256**, respectively. Each active region includes a resistor having a doped feature **236** formed in the corresponding semiconductor mesa and extended to the semiconductor substrate **110** in the corresponding active region. In the present example, the semiconductor structure **250** includes a first resistor, a second

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resistor and a third resistor associated with the first, second and third semiconductor mesas (120C, 120D and 120E), respectively.

Each resistor is connected to the two terminals: a first contact 258 landing on the semiconductor substrate as a first terminal and a second contact 260 landing on the respective semiconductor mesa as a second terminal.

Furthermore, the semiconductor structure 250 includes various conductive features 262 in the interconnect structure. The conductive features 260 may include metal lines and via features configured to couple the plurality of the resistors in series. Particularly, the second contact 260 of the first resistor is electrically connected to the first contact 258 of the second resistor. The second contact 260 of the second resistor is electrically connected to the first contact 258 of the third resistor, and so on (if more resistors are in series connection). Thus integrated resistor is a two terminal passive device. In this example, the first contact 258 of the first resistor serves as a first terminal and the second contact 260 of the third resistor serves as a second terminal.

FIG. 15 is a sectional view of a semiconductor structure 270 constructed according to another embodiment of the present disclosure. The semiconductor structure 270 includes a plurality of resistors connected in parallel. FIG. 15 only shows three resistors for illustration. Each resistor is formed in a semiconductor mesa.

The semiconductor structure 270 includes various STI features 122 formed in the semiconductor substrate 110, defining an active region. Multiple semiconductor mesas are formed on the semiconductor substrate 110 within the active region. In the present embodiment, exemplary three semiconductor mesas 120F, 120G and 120H are formed on the active region. multiple resistors are formed on the semiconductor mesas, respectively. In the present example, the semiconductor structure 250 includes a first resistor, a second resistor and a third resistor associated with the first, second and third semiconductor mesas (120F, 120GD and 120H), respectively.

Each resistor includes a doped feature 236 formed in the corresponding semiconductor mesa, extended to the semiconductor substrate 110. The doped features 236 are merged together in the semiconductor substrate 110. Each resistor has two terminals: a first contact 258 landing on the semiconductor substrate 110 as a common contact to the resistors in the active region; and a second contact 260 landing on the respective semiconductor mesa as a second terminal.

Accordingly, the three resistors are coupled together to form a two terminal passive device: the first contact 258 as a first terminal and the second contacts 260 electrically connected together through the conductive features 262 to form a second terminal.

Thus, the present disclosure provides one embodiment of a semiconductor structure. The semiconductor structure includes a semiconductor substrate having a first region and a second region; a first semiconductor mesa formed on the semiconductor substrate within the first region; a second semiconductor mesa formed on the semiconductor substrate within the second region; and a field effect transistor (FET) formed on the semiconductor substrate. The FET includes a first doped feature of a first conductivity type formed in a top portion of the first semiconductor mesa; a second doped feature of a second conductivity type formed in a bottom portion of the first semiconductor mesa, the second semiconductor mesa, and a portion of the semiconductor substrate between the first and second semiconductor mesas; a channel in a middle portion of the first semiconductor mesa and interposed between the source and drain; and a gate formed on sidewall of the first semiconductor mesa.

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The present disclosure also provides another embodiment of a semiconductor resistor. The semiconductor resistor includes a semiconductor substrate having a first active region; a first semiconductor mesa formed on the semiconductor substrate within the first active region; a first resistor formed on the semiconductor substrate within the first active region; and a first contact and a second contact connected to two ends of the first resistor, respectively. The first resistor includes a first doped feature formed on the first semiconductor mesa and extended to the semiconductor substrate within the first active region. The first contact lands on the semiconductor substrate and the second contact lands on the first semiconductor mesa.

The present disclosure also provides an embodiment of a method of forming a tunnel field effect transistor (TFET). The method includes forming a first semiconductor mesa and a second semiconductor mesa on a semiconductor substrate; performing a first implantation to form a drain of a first type conductivity, wherein the drain is a continuous doped feature extended from the first semiconductor mesa to the second semiconductor mesa through the semiconductor substrate; forming a first dielectric layer on the semiconductor substrate and sidewall of the first and second semiconductor mesas; forming a gate stack on the sidewall of the first semiconductor mesa and extending horizontally on the first dielectric layer; forming a second dielectric layer on the first dielectric layer and a horizontal portion of the gate stack; removing a portion of the gate stack uncovered by the second dielectric layer; and forming, on the first semiconductor mesa, a source having a second type conductivity opposite to the first type conductivity.

The foregoing has outlined features of several embodiments. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A semiconductor structure, comprising:

a semiconductor substrate having a first active region;  
a first semiconductor mesa formed on the semiconductor substrate within the first active region;  
a first resistor formed on the semiconductor substrate within the first active region, wherein the first resistor includes a first doped feature formed on the first semiconductor mesa and extended to the semiconductor substrate within the first active region; and  
a first contact and a second contact connected to two ends of the first resistor, respectively,  
wherein the first contact lands on the semiconductor substrate and the second contact lands on the first semiconductor mesa, wherein the first doped feature formed on the first semiconductor mesa extends from the second contact to the semiconductor substrate, wherein the first doped feature has a same type of conductivity extending from the second contact to the semiconductor substrate.

2. The semiconductor structure of claim 1, wherein the semiconductor substrate includes a second active region separated from the first active region by a shallow trench isolation (STI) feature, and the semiconductor structure further includes:

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a second semiconductor mesa formed on the semiconductor substrate within the second active region;  
 a second resistor formed on the semiconductor substrate within the second active region, wherein the second resistor includes a second doped feature formed on the second semiconductor mesa and extended to the semiconductor substrate within the second active region; and  
 a third contact and a fourth contact connected to two ends of the second resistor, respectively,  
 wherein the third contact lands on the semiconductor substrate and the fourth contact lands on the first semiconductor mesa, and the second resistor is connected with first resistor in series.

3. The semiconductor structure of claim 2, further comprising an interconnect feature configured to electrically connect the second and third contacts.

4. The semiconductor structure of claim 1, wherein the semiconductor substrate has the conductivity type, and wherein the first doped feature has a doping concentration greater than that of the semiconductor substrate.

5. A semiconductor device, comprising:

a substrate having a first region and a second region;  
 a first mesa formed on the substrate within the first region;  
 a second mesa formed on the substrate within the second region; and

a field effect transistor (FET) formed on the substrate, wherein the FET includes

a first feature of a first conductivity type formed in a first portion of the first mesa;

a second feature of a second conductivity type formed in a second, different portion of the first mesa, the second mesa, and a portion of the substrate between the first and second mesas, wherein one of the first and second features is a source and the other of the first and second features is a drain;

a channel in a middle portion of the first mesa and interposed between the source and drain;

a gate formed on sidewall of the first mesa,

a drain pickup feature formed in a top portion of the second semiconductor mesa, the drain pickup feature includes a doping species of the second conductivity type, and the drain pickup feature has a doping concentration different than that of the drain.

6. The semiconductor device of claim 5, wherein the second conductivity type is opposite to the first conductivity type,

the FET is a vertical tunnel field effect transistor (TFET), the first feature is a source of the vertical TFET, and the second feature is a drain of the vertical TFET.

7. The semiconductor device of claim 6, wherein the second feature is a continuous feature extending from the first mesa to the second mesa through the substrate.

8. The semiconductor device of claim 6, wherein the first mesa has a first top surface, the second mesa has a second top surface, and the first and second top surfaces are coplanar.

9. A semiconductor structure, comprising:

a semiconductor substrate having a first region and a second region;

a first semiconductor mesa formed on the semiconductor substrate within the first region;

a second semiconductor mesa formed on the semiconductor substrate within the second region; and

a field effect transistor (FET) formed on the semiconductor substrate, wherein the FET includes:

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a first doped feature of a first conductivity type formed in a top portion of the first semiconductor mesa, wherein the first doped feature is a source of the FET;

a second doped feature of a second conductivity type formed in a bottom portion of the first semiconductor mesa, the second semiconductor mesa, and a portion of the semiconductor substrate between the first and second semiconductor mesas, wherein the second doped feature is a drain of the FET, wherein the second conductivity type is opposite to the first conductivity type;

a channel in a middle portion of the first semiconductor mesa and interposed between the source and drain; and

a gate formed on sidewall of the first semiconductor mesa; and

a drain contact that is connected to the drain and lands on the second semiconductor mesa;

a source contact that is connected to the source and lands on the first semiconductor mesa; and

a gate contact that lands on a horizontal portion of the gate and is configured between the source and drain.

10. The semiconductor structure of claim 9, wherein the FET is a vertical tunnel field effect transistor (TFET).

11. The semiconductor structure of claim 9, wherein the second doped feature is a continuous feature extending from the first semiconductor mesa to the second semiconductor mesa through the semiconductor substrate.

12. The semiconductor structure of claim 9, wherein the first semiconductor mesa has a first top surface, the second semiconductor mesa has a second top surface, and the first and second top surfaces are coplanar.

13. The semiconductor structure of claim 9, wherein the top portion of the first semiconductor substrate includes a semiconductor material different from that of the bottom portion of the first semiconductor mesa.

14. The semiconductor structure of claim 9, wherein the vertical TFET further includes a drain pickup feature formed in a top portion of the second semiconductor mesa,

the drain pickup feature includes a doping species of the second conductivity type, and

the drain pickup feature has a doping concentration greater than that of the drain.

15. The semiconductor structure of claim 9, wherein each of the first and second semiconductor mesas has a sidewall profile with a tilt angle in a sectional view, wherein

the tilt angle is measured relative to a top surface of the semiconductor substrate, and

the tilt angle is less than 90° and greater than 45°.

16. The semiconductor structure of claim 9, wherein each of the first and second semiconductor mesas has a round shape in a top view.

17. The semiconductor structure of claim 9, wherein the gate includes

a gate dielectric layer having a high k dielectric material; and

a gate electrode having a metal.

18. The semiconductor structure of claim 9, further comprising:

a third semiconductor mesa formed on the semiconductor substrate in a third region;

a resistor having a doped feature formed in the third semiconductor mesa and extended to the semiconductor substrate; and

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a first contact and a second contact connected to two ends of to the resistor, respectively.

**19.** The semiconductor structure of claim **18**, wherein the first contact lands on the semiconductor substrate and the second contact lands on the third semiconductor mesa. 5

**20.** The semiconductor structure of claim **18**, further comprising a plurality of shallow trench isolation (STI) features formed in the semiconductor substrate and defining a first active region and a second active region, wherein

the first and second semiconductor mesas are disposed on 10 the first active region, and

the third semiconductor mesa is disposed on the second active region.

\* \* \* \* \*

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